

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Keisuke TSUKAMOTO et al.

Appln. No.:

Filed: HERewith

For: A SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE AND A
METHOD OF MANUFACTURING THE SAME

* * *

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

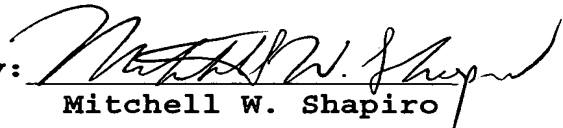
Applicants wish to make of record the documents cited
in prior Application No. 10/196,166 filed July 17, 2002,
whether cited by Applicants or by the Patent Office. The
documents are listed on the attached Form PTO-1449.

Respectfully submitted,

MWS:lmb

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By:


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February 26, 2004

FORM PTO-1449				Atty. Docket No. XA-9721A		Appln. No.	
LIST OF DOCUMENTS CITED BY APPLICANT							
				Applicant Keisuke TSUKAMOTO et al.			
				Filing Date HEREWITH		Group	
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Sub-class	Filing Date
	AA	5,946,230	8/99	Shimizu et al.	257	314	
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
FOREIGN PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Country	Class	Sub-class	Translation
	AJ						
	AK						
	AL						
	AM						
	AN						
	AO						
OTHER (including author, title, date, pertinent pages, etc.)							
	AP	Kim et al., "A Novel 4.6F ² NOR Cell Technology With Lightly Doped Source (LDS) Junction For High Density Flash Memories," IEDM (International Electron Devices Meeting), 1998, pp. 979-982.					
	AQ						
Examiner				Date Considered			
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.							